



# 3DD66

## NPN Silicon Low Frequency High Power Transistor



### Features:

1. Using triple-diffusion, low resistance liner process. Heavy out-put Current, small saturation voltage drop. Excellent out-put characteristic.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify, power adjustment, DC conversion.
4. Quality Class: JP, JT, JCT, GS, G, G+

### TECHNICAL DATA:

( $T_a = 25^\circ\text{C}$ )

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	$V_{CEO}$	V	30	50	80	110	150	
Emitter-Base Voltage	$V_{EBO}$	V	3					
Max. Collector Current	$I_{CM}$	A	7.5					
Max. Collector Dissipation	$P_{CM}$	W	75					$T_c: 75^\circ\text{C}$
Junction Temperature	$T_{jm}$	$^\circ\text{C}$	175					
Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-55~+175					
Collector-Emitter Leakage Current	$I_{CEO}$	mA	Max.: 3.0					$V_{CE}=20\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.: 1.5					$I_C=3.75\text{A}, I_B=0.75\text{A}$
DC Current Gain	$h_{FE}$		Min.: 10					$V_{CE}=5\text{V}, I_C=3.75\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	$I_C=10\text{mA}$
			30	50	80	110	150	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	3					$I_E=15\text{mA}$

### $h_{FE}$ Colored:

Color	Brown	Red	Orange
$h_{FE}$	10~20	20~30	30~

### Outline and Dimensions: